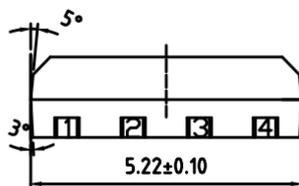


GS302 Programmable Linear Hall-Effect IC

- GaAs + Si Hybrid Programmable Linear Hall-Effect IC
- Single power supply : VDD 3V ~ 5.5V
- Analog Fixed or Ratiometric Output
- Wide ambient Temperature Range : Ta -40°C ~ 125°C
- Quick response for magnetic field with wide bandwidth
- Programmable via One Wire Interface at Vout Pin

Output Characteristics



引脚编号 Pinning	引脚名称 Pinning Define
1	VDD
2	GND
3	VOUT
4	VBIAS

Figure1. Definition of sensitivity direction

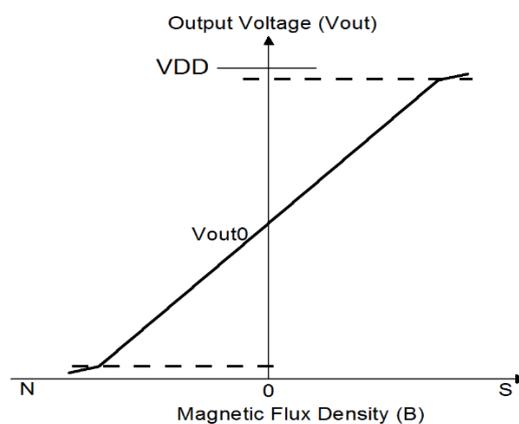
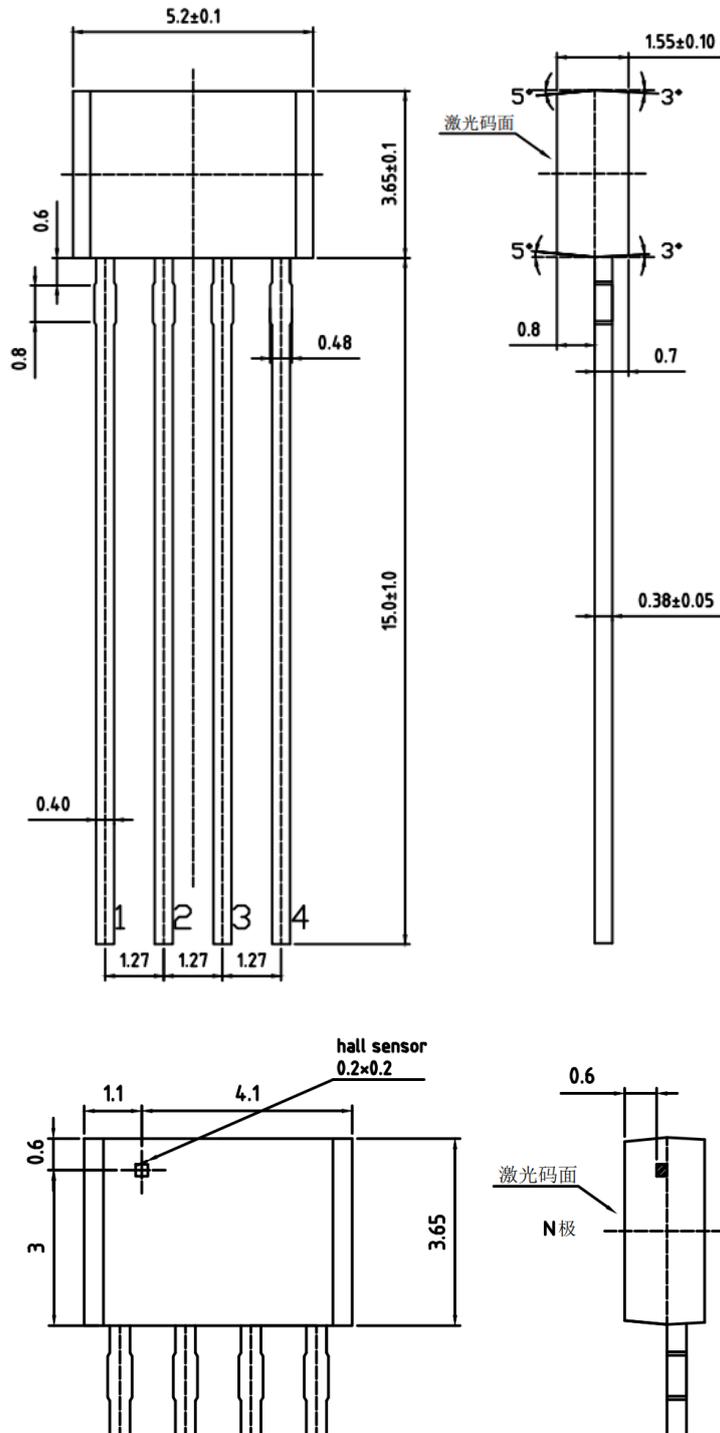


Figure 2. Output Characteristics of GS302

Dimensional Drawing (Unit MM)



Absolute Maximum Rating

Table 1 . GS302 Working conditions

Characteristics	Symbol	Condition	Min	Typ	Max	Unit
Supply Voltage	V_{DD}	$T_a = 25^\circ\text{C}$	-0.3		6.5	V
Output Current	I_{out}	$T_a = 25^\circ\text{C}$	-45		45	mA
Analog output	V_{out}/V_{bias}	$T_a = 25^\circ\text{C}$	0.4		$V_{DD}-0.4$	V
Storage Temp.	T_s		-40		150	$^\circ\text{C}$
Operation Temp.	T_a		-40		125	$^\circ\text{C}$

Operation Conditions

Table 2. Electric and magnetic characteristics Ta=-40 to 85°C

Characteristics	Symbol	Condition	Min	Type	Max	Unit
Supply Voltage	V_{DD}	Ta = 25°C	3		5.5	V
Current Consumption	I_s	In Programming @ Ta = 25°C			33	mA
		In normal operation @Ta=25°C		6.5	11	mA
Sensitivity Range	V_{hrange}	Ta = 25°C	0.5		200	mV/mT
Response Time	T_r	C=20pF Vh=100 mV/mT @ Ta = 25°C			6	μs
Signal bandwidth	B_w			250	500	KHz
Load Capacitance	C_L	Ta = 25°C		20p	10n	F
Quiescent Voltage of Differential Output at Ta 25°C	V_0-V_{bias}	M1	-0.01		0.01	V
		M2	-0.005		0.005	V
Quiescent Voltage of Differential Output In -40°C~85°C	V_0-V_{bias}	M1	-0.02		0.02	V
		M2	-0.01		0.01	V

-GS302 Programmable Linear Hall-Effect IC-

Characteristics	Symbol	Condition	Min	Type	Max	Unit
Quiescent Voltage (fixed output) Ta=25°C	V ₀	M1	2.490		2.510	V
		M2	1.640		1.660	V
Quiescent Voltage (fixed output) In -40°C~85°C	V ₀	M1	2.480		2.520	V
		M2	1.635		1.665	V
Sensitivity drift through temperature (fixed output)	ΔS/S(25°C)	M1 In -40°C~25°C	-1.5		1.5	%
		M1 In 25°C~85°C	-1.5		1.5	%
		M2 In -40°C~25°C	-1.5		1.5	%
		M2 In 25°C~85°C	-1.5		1.5	%
Output Saturation	V _{out-SatH}		V _{DD} -0.5			V

Characteristics	Symbol	Condition	Min	Type	Max	Unit
Voltage	$V_{out-SatL}$				0.5	V
Error of sensitivity (ratio metric output) In $-40^{\circ}\text{C}\sim 85^{\circ}\text{C}$	S_{erro}	V_{DD} in range 4.75~5.25V	-0.4		0.4	%
Error of Quiescent Voltage (ratio metric output) In $-40^{\circ}\text{C}\sim 85^{\circ}\text{C}$	V_{0erro}	V_{DD} in range 4.75~5.25V	-0.3		0.3	%
Linearity Error	ρ	$V_{DD}=5\text{V}$, $V_0=2.500\text{V}$, $V_{out}=2.500\pm 2.000\text{V}@ \pm 20\text{mT}$	-0.5		0.5	%

Note:

Fixed output Mode:

M1 : $V_{DD}=5\text{V}$, $V_0=2.500\text{V}$ or V_{bias} , $V_{out} = V_0 \pm 2.000\text{V}@ \pm 20\text{mT}$, sensitivity : 100 mV/mT ;

M2 : $V_{DD}=3.3\text{V}$, $V_0=1.650\text{V}$ or V_{bias} , $V_{out} = V_0 \pm 1.000\text{V}@ \pm 20\text{mT}$, sensitivity : 50 mV/mT ;

Characteristics Definitions

1. Sensitivity V_{hrange} [mV/mT].

Sensitivity is defined as the slope of the approximate straight line calculated by the least square method, using data of OUT voltage (V_{out}) when the magnetic flux density (B) is swept within the range of input magnetic flux density (B_{in}).

2. Linearity Error ρ [%F.S.].

Linearity error is defined as the ratio of the maximum perpendicular deviation (MPD) to the full scale (F.S.), where MFD is the maximum difference between the OUT voltage (V_{out}) and the approximate straight line calculated in the sensitivity definition. Definition formula is shown in below:

$$\rho = 100 * \frac{MFD}{F.S.} = 100 * \frac{MFD}{V_H - V_L}$$

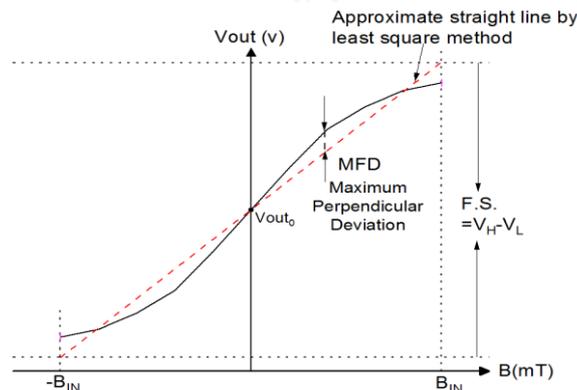


Figure 3. Output characteristics of GS302

3. Ratiometric output error of sensitivity V_{0erro} [%] and ratiometric output error of Quiescent voltage S_{erro} [%].

The quiescent voltage (V_{out0}) of the GS302 is constant, which means that it does not vary with the VDD. Error of Quiescent Voltage is defined as the difference between the V_H (or V_{out0}) when the VDD is changed from 5.0v to VDD_1 ($4.75v < VDD_1 < 5.25v$ or $4.5v < VDD_1 < 5.5v$). Definition formula is shown

in blow:

$$S_{\text{erro}} = \left[\frac{V_{\text{out}}(VDD)}{V_{\text{out}}(5v)} - \frac{VDD}{5} \right] * 100$$

$$V_{0\text{erro}} = \left[\frac{V_0(VDD)}{V_0(5v)} - \frac{VDD}{5} \right] * 100$$

4. Rise response time T_r [μs].

Rise response time is defined as the time delay from the 90% of input magnetic field (B) to the 90% of the OUT voltage (V_{out}) under the pulse input of magnetic flux density.

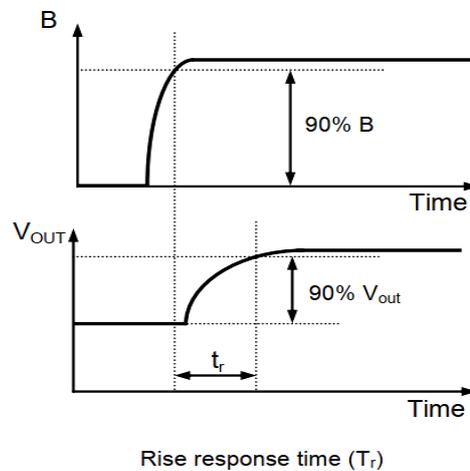
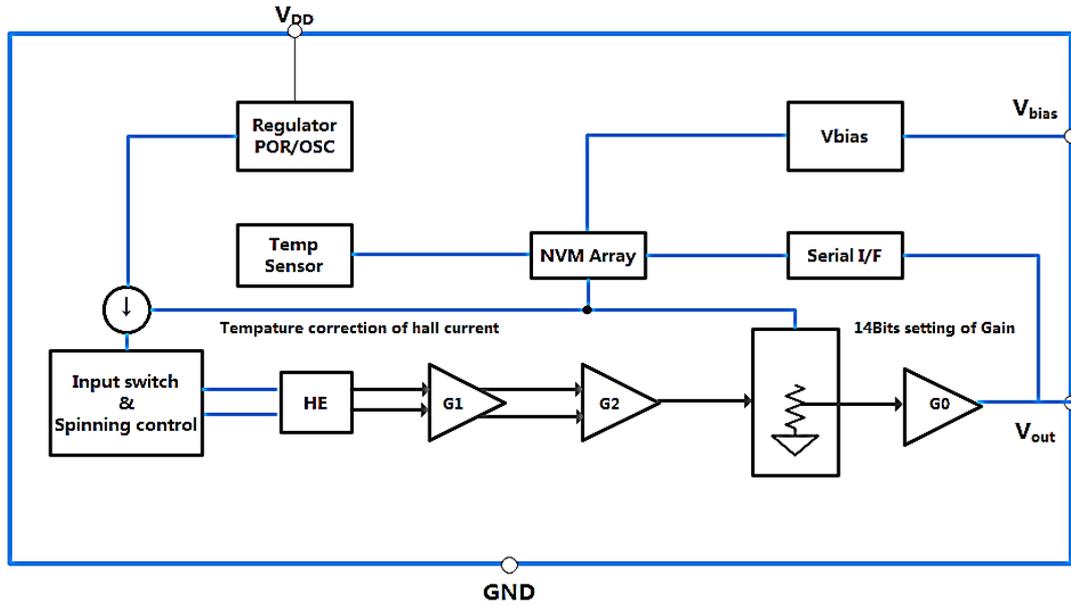


Figure 4. Definition of response time

5. Output Saturation Voltage $V_{\text{out-SatH}}$ and $V_{\text{out-SatL}}$.

Output saturation voltage is defined as the saturated output at a fixed output current. $V_{\text{out-SatH}}$ is defined as the chip's output voltage when the output current is -2 or 0.5mA in the positive magnetic field, and $V_{\text{out-SatL}}$ is the chip's output voltage when the output current is -2 or 0.5mA in the negative magnetic field.

Function Block Diagram



Application Circuits

